60 V / 50 V, 170 mA / 160 mA N/P-channel Trench MOSFET
18 January 2018 Product data sheet

1. General description

Complementary N/P-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- · Very fast switching
- · ElectroStatic Discharge (ESD) protection

3. Applications

- · Relay driver
- · High-speed line driver
- · Level shifter
- Power supply converter

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
TR1 (N-channe	TR1 (N-channel)						
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	170	mA
TR1 (N-channe	TR1 (N-channel), Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 100 mA; T_j = 25 °C		-	3	4.5	Ω
TR2 (P-channe	l)						
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-50	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-	-160	mA
TR2 (P-channel), Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -100 mA; T_j = 25 °C		-	4.5	7.5	Ω

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	□6 □5 □4	D1 D2
2	G1	gate TR1		
3	D2	drain TR2	0	G1 A T G2
4	S2	source TR2	1 2 3	
5	G2	gate TR2	TSSOP6 (SOT363)	
6	D1	drain TR1		S1 S2 017aaa262

6. Ordering information

Table 3. Ordering information

Type number	Package	Package					
	Name	Description	Version				
NX6020CAKS	TSSOP6	plastic surface-mounted package; 6 leads	SOT363				

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
NX6020CAKS	2A%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

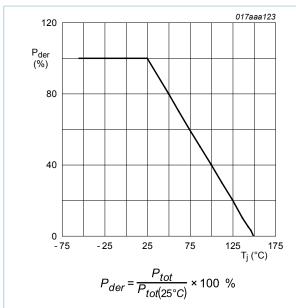
Symbol	Parameter	Conditions		Min	Max	Unit
TR1 (N-char	nnel)			'	'	_
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	170	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	100	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	680	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	220	mW
			[1]	-	255	mW
		T _{sp} = 25 °C		-	1.06	W
TR2 (P-char	nnel)		1		1	
V _{DS}	drain-source voltage	T _j = 25 °C		-	-50	٧
V _{GS}	gate-source voltage			-20	20	٧
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-160	mA
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-100	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	-640	mA
P _{tot}	total power dissipation	ation T _{amb} = 25 °C	[2]	-	280	mW
			[1]	-	320	mW
		T _{sp} = 25 °C		-	990	mW
Per device					1	
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	330	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
TR1 (N-char	nnel), Source-drain diode	-				
I _S	source current	T _{amb} = 25 °C	[1]	-	170	mA
TR2 (P-char	nnel), Source-drain diode	1			1	
I _S	source current	T _{amb} = 25 °C	[1]	-	-160	mA

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².

NX6020CAKS

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.

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Normalized total power dissipation as a function of junction temperature

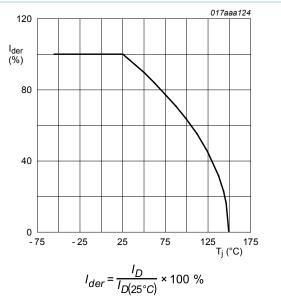
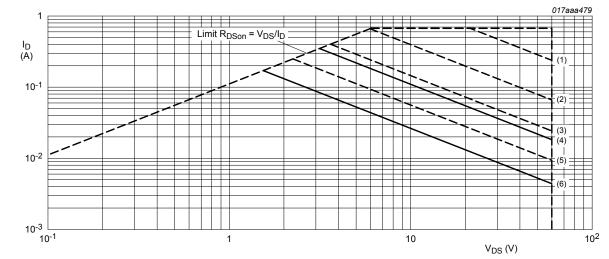


Fig. 2. Normalized continuous drain current as a function of junction temperature



 I_{DM} = single pulse (1) t_p = 100 μ s (2) t_p = 1 ms (3) t_p = 10 ms (4) DC; T_{sp} = 25 °C (5) t_p = 100 ms (6) DC; T_{amb} = 25 °C; drain mounting pad 1 cm²

TR1: Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-Fig. 3. source voltage

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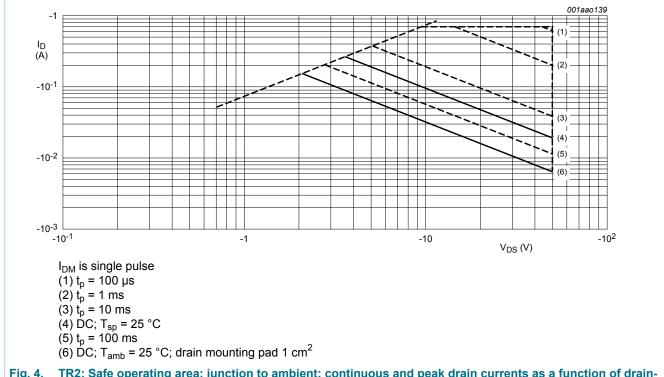


Fig. 4. TR2: Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
TR1 (N-cha	nnel)						
R _{th(j-a)}	thermal resistance	in free air	[1]	-	500	560	K/W
	from junction to ambient		[2]	-	450	480	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	115	K/W
TR2 (P-cha	nnel)						
R _{th(j-a)}	thermal resistance in free air from junction to ambient	in free air	[1]	-	390	445	K/W
		[2]	-	340	390	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	130	K/W
Per device							
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	300	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².

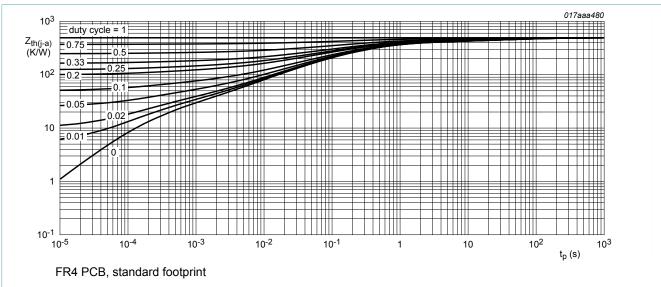


Fig. 5. TR1: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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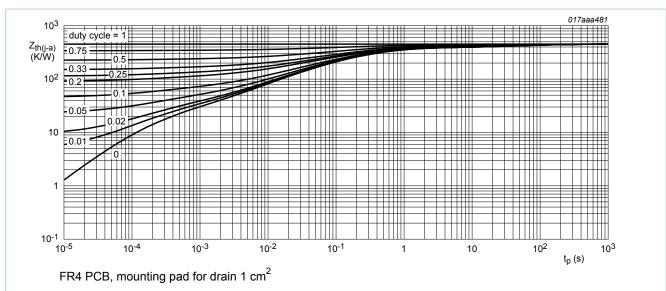


Fig. 6. TR1: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

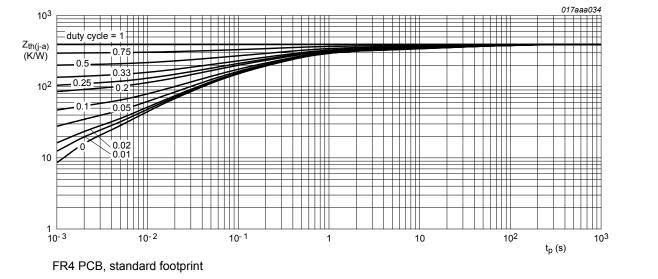
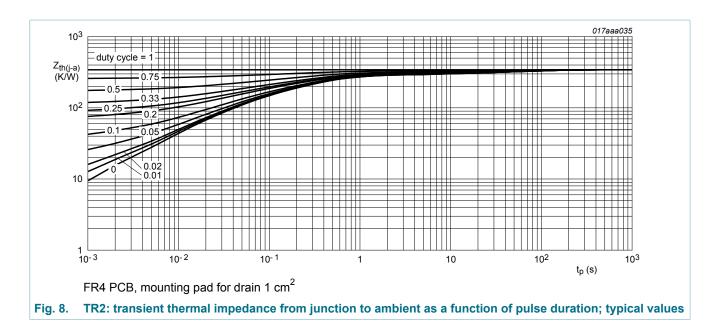


Fig. 7. TR2: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

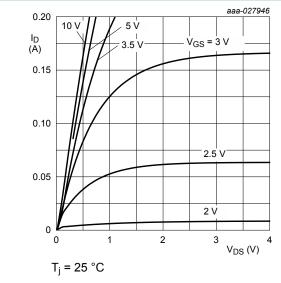
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
TR1 (N-cha	nnel), Static characteristic	s				
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μA
		V_{DS} = 60 V; V_{GS} = 0 V; T_j = 150 °C	-	-	10	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	2	μΑ
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	2	μA
		V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	0.5	μA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	0.5	μΑ
		V _{GS} = 5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V_{GS} = -5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 100 mA; T _j = 25 °C	-	3	4.5	Ω
	resistance	V_{GS} = 10 V; I_D = 100 mA; T_j = 150 °C	-	6.2	9.2	Ω
		$V_{GS} = 5 \text{ V}; I_D = 100 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	3.7	5.2	Ω
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_D = 200 mA; T_j = 25 °C	-	230	-	mS
TR2 (P-chai	nnel), Static characteristic	s				
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -10 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	-50	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-1.1	-1.6	-2.1	V
I _{DSS}	drain leakage current	V _{DS} = -50 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
		V _{DS} = -50 V; V _{GS} = 0 V; T _j = 150 °C	-	-	-2	μΑ
I _{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-10	μΑ
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-10	μΑ
R _{DSon}	drain-source on-state	V_{GS} = -10 V; I_D = -100 mA; T_j = 25 °C	-	4.5	7.5	Ω
	resistance	V_{GS} = -10 V; I_D = -100 mA; T_j = 150 °C	-	8	13.5	Ω
		V_{GS} = -5 V; I_D = -100 mA; T_j = 25 °C	-	5.7	8.5	Ω
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_D = -100 mA; T_j = 25 °C	-	150	-	mS
TR1 (N-cha	nnel), Dynamic characteris	stics	'		,	
Q _{G(tot)}	total gate charge	V_{DS} = 30 V; I_{D} = 200 mA; V_{GS} = 4.5 V;	-	0.33	0.43	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q_{GD}	gate-drain charge		-	0.09	_	nC

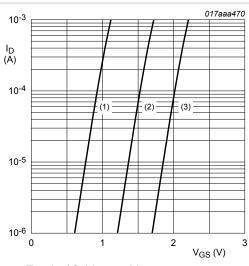
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	11	17	pF
C _{oss}	output capacitance	T _j = 25 °C	-	3.4	-	pF
C _{rss}	reverse transfer capacitance		-	1.4	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 40 V; R_{L} = 250 Ω ; V_{GS} = 10 V;	-	6	12	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	7	-	ns
t _{d(off)}	turn-off delay time		-	20	40	ns
t _f	fall time		-	14	-	ns
TR2 (P-chai	nnel), Dynamic character	istics				
Q _{G(tot)}	total gate charge	V_{DS} = -25 V; I_{D} = -200 mA; V_{GS} = -5 V;	-	0.26	0.35	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q_{GD}	gate-drain charge		-	0.09	-	nC
C _{iss}	input capacitance	V _{DS} = -25 V; f = 1 MHz; V _{GS} = 0 V;	-	24	36	pF
C _{oss}	output capacitance	T _j = 25 °C	-	4.5	-	pF
C _{rss}	reverse transfer capacitance		-	1.3	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -30 V; R_L = 250 Ω ; V_{GS} = -10 V;	-	13	26	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	11	-	ns
$t_{d(off)}$	turn-off delay time		-	48	96	ns
t _f	fall time		-	25	-	ns
TR1 (N-cha	nnel), Source-drain diode	characteristics				
V _{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V; T _j = 25 °C	0.47	0.7	1.2	V
TR2 (P-chai	nnel), Source-drain diode	characteristics	'			
V_{SD}	source-drain voltage	I _S = -115 mA; V _{GS} = 0 V; T _i = 25 °C	-0.48	-0.85	-1.2	V

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TR1: Output characteristics: drain current as a Fig. 9. function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C; V_{DS} = 5 \, V$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 10. TR1: Sub-threshold drain current as a function of gate-source voltage

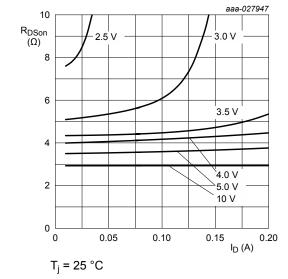
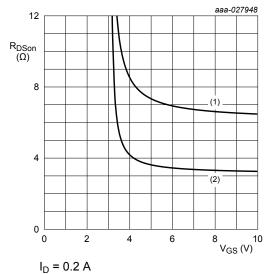


Fig. 11. TR1: Drain-source on-state resistance as a function of drain current; typical values



(1) $T_j = 150 \, ^{\circ}C$

(2) $T_j = 25 \,^{\circ}\text{C}$

Fig. 12. TR1: Drain-source on-state resistance as a function of gate-source voltage; typical values

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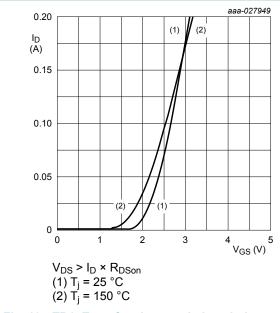
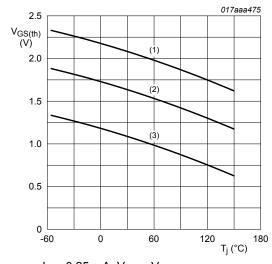


Fig. 13. TR1: Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 15. TR1: Gate-source threshold voltage as a function of junction temperature

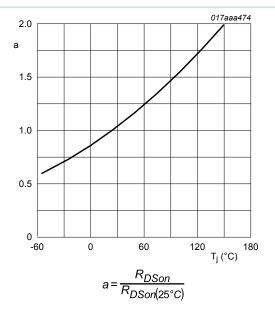
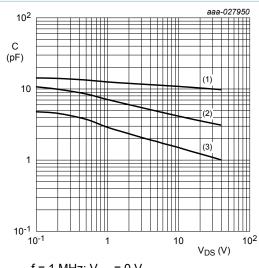


Fig. 14. TR1: Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss} (2) C_{oss} (3) C_{rss}

Fig. 16. TR1: Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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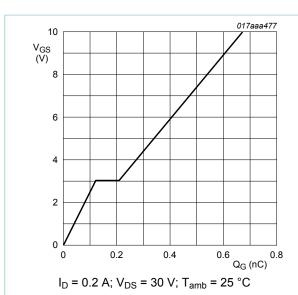


Fig. 17. TR1: Gate-source voltage as a function of gate charge; typical values

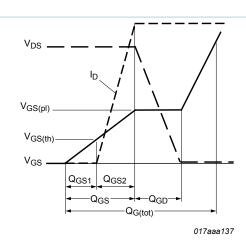


Fig. 18. TR1: Gate charge waveform definitions

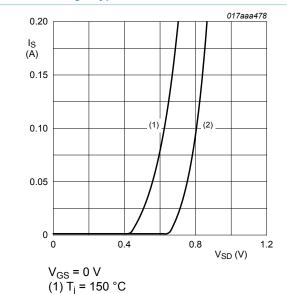


Fig. 19. TR1: Source current as a function of sourcedrain voltage; typical values

(2) $T_i = 25 \,^{\circ}C$

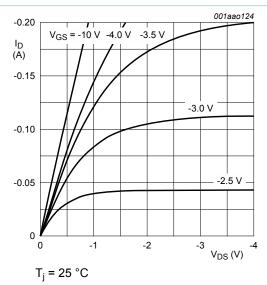
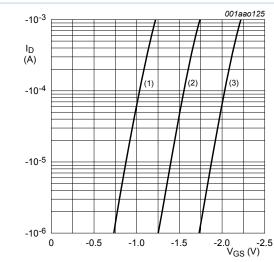


Fig. 20. TR2: Output characteristics: drain current as a function of drain-source voltage; typical values

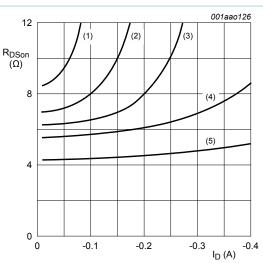
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 $T_i = 25 \,^{\circ}C; \, V_{DS} = -5 \,^{\circ}V$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 21. TR2: Sub-threshold drain current as a function of gate-source voltage



T_i = 25 °C

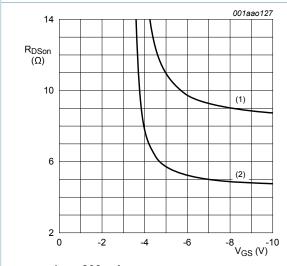
 $(1) V_{GS} = -3.0 V$

 $(2) V_{GS} = -3.5 V$

 $(3) V_{GS} = -4.0 V$

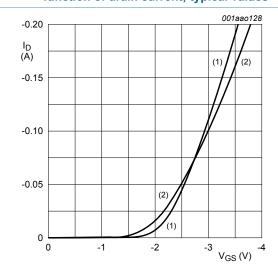
(4) $V_{GS} = -5.0 \text{ V}$ (5) $V_{GS} = -10.0 \text{ V}$

Fig. 22. TR2: Drain-source on-state resistance as a function of drain current; typical values



 I_D = -200 mA (1) T_j = 150 °C (2) T_j = 25 °C

Fig. 23. TR2: Drain-source on-state resistance as a function of gate-source voltage; typical values



 $V_{DS} > I_D \times R_{DSon}$

(1) $T_j = 25 \,^{\circ}\text{C}$ (2) $T_j = 150 \,^{\circ}\text{C}$

Fig. 24. TR2: Transfer characteristics: drain current as a function of gate-source voltage; typical values

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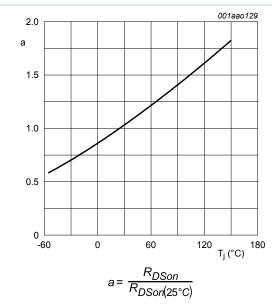
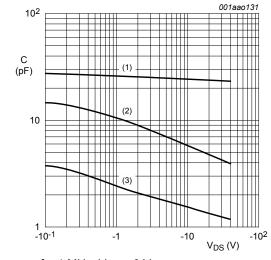


Fig. 25. TR2: Normalized drain-source on-state resistance as a function of junction temperature; typical values

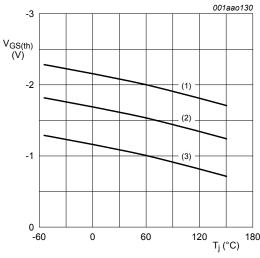


 $f = 1 MHz; V_{GS} = 0 V$

 $\begin{array}{c} \text{(1) } C_{iss} \\ \text{(2) } C_{oss} \end{array}$

(3) C_{rss}

Fig. 27. TR2: Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



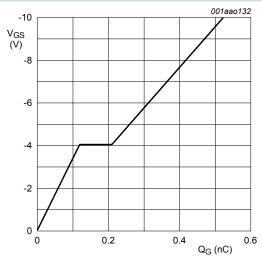
 $I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$

(1) maximum values

(2) typical values

(3) minimum values

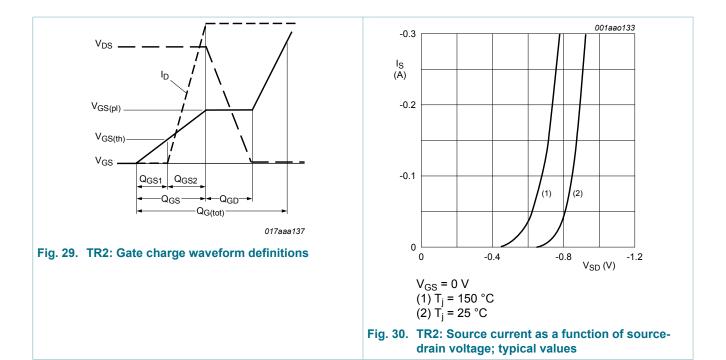
Fig. 26. TR2: Gate-source threshold voltage as a function of junction temperature



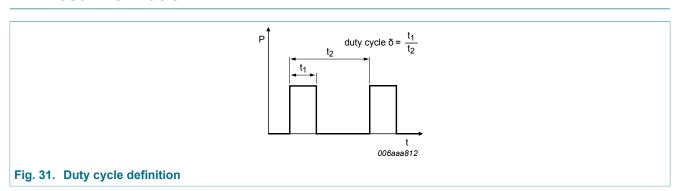
 I_D = -200 mA; V_{DS} = -25 V; T_{amb} = 25 °C

Fig. 28. TR2: Gate-source voltage as a function of gate charge; typical values

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11. Test information



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12. Package outline

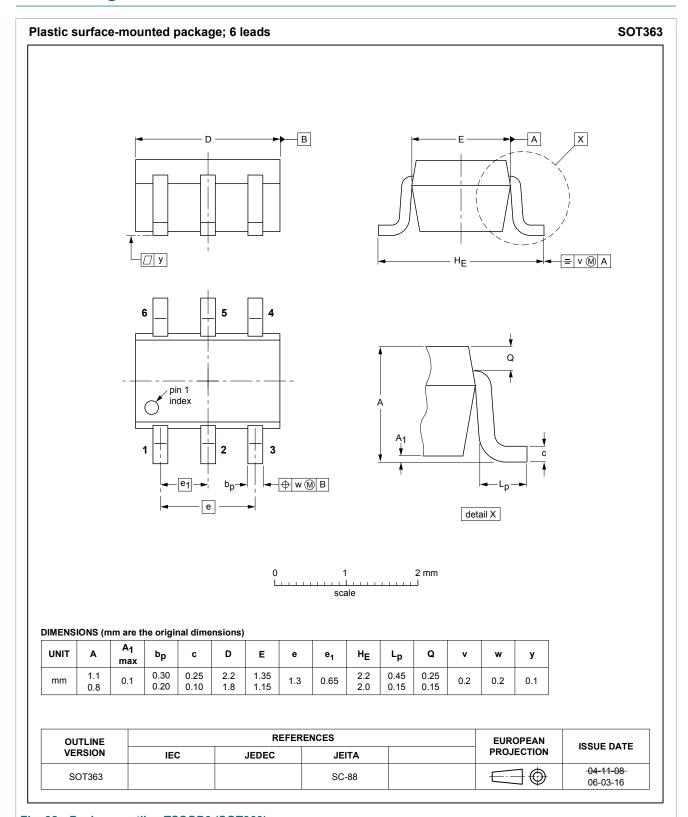
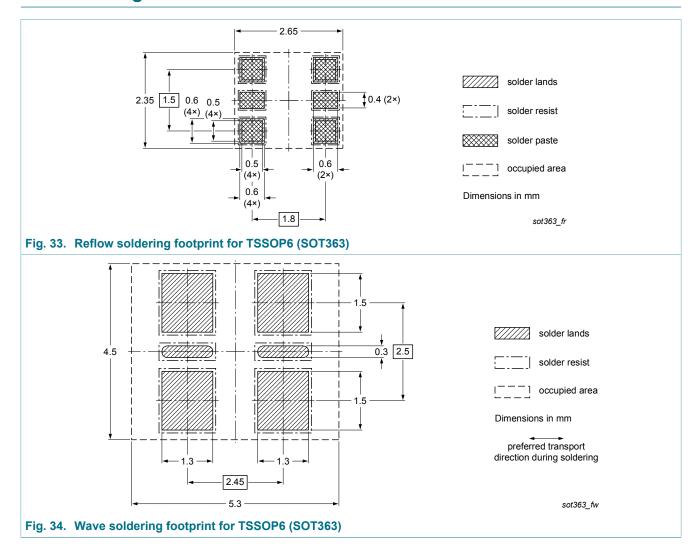


Fig. 32. Package outline TSSOP6 (SOT363)

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13. Soldering



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14. Revision history

Table 8. Revision history

- sale of the territory							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
NX6020CAKS v.2	20180118	Product data sheet	-	NX6020CAKS v.1			
Modifications:	 Data sheet status changed to Product. Section: Limiting values, ESD maximum rating removed. 						
NX6020CAKS v.1	20171220	Preliminary data sheet	-	-			

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
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